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INT-A-PAK Power Module Thyristor/Diode, 300 A



INT-A-PAK

PRODUCT SUMMARY					
I _{T(AV)}	300 A				
Туре	Modules - Thyristor, Standard				
Package	INT-A-PAK				
Circuit	SCR/diode doubler circuit, negative control				

FEATURES

- · Electrically isolated base plate
- 3000 V_{RMS} isolating voltage



- · Industrial standard package
- Simplified mechanical designs, rapid assembly
- High surge capability
- Large creepage distances
- UL approved file E78996
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Battery chargers
- Welders
- Power converters
- Alternators

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
V _{DRM} /V _{RRM}		800	V		
I _{T(AV)}	53 °C	300	Α		
1	50 Hz	6500	٨		
I _{TSM}	60 Hz	6900	Α		
l ² t	50 Hz	214	kA ² s		
1-1	60 Hz	195	KA-5		
I²√t		2140	kA²√s		
T _J	Range	-40 to 140	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS						
TYPE NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} /V _{DSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA			
VS-VSKL300/08PbF	800	900	50			



ON-STATE CONDUCTION													
PARAMETER	SYMBOL		VALUES	UNITS									
Maximum average on-state current	L	190° conducti	180° conduction half sine wave			Α							
at case temperature	I _{T(AV)}	180 Conducti	on nan sine wave		53	°C							
Maximum RMS on-state current	I _{T(RMS)}	As AC switch			116								
		t = 10 ms	No voltage		6600								
Maximum peak, one-cycle on-state, non-repetitive		t = 8.3 ms	reapplied		6900	Α							
surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		5500								
	·	reapplied	Sine half wave,									5800	
Maximum I ² t for fusing		t = 10 ms	No voltage	 initial T_J = T_J maximum 	214	kA ² s							
	l ² t	t = 8.3 ms	reapplied		195								
	1-1	t = 10 ms	100 % V _{RRM}		151								
		t = 8.3 ms	reapplied		138								
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 1	0 ms, no voltage re	eapplied	2140	kA²√s							
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x	$I_{T(AV)} < I < \pi \times I_{T(AV)}$	T _J maximum	0.796	V							
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}),$	$(I > \pi \times I_{T(AV)}), T_J$ maximum			V							
Low level value on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T_J maximum			0.972	mΩ							
High level value on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)})$, T_J maximum			0.88	11122							
Maximum on-state voltage drop	V _{TM}	T _J = 25 °C, 50	0.4.1	SCR	1.35	V							
waxiinum on-state voitage drop	V _{FM}	1J = 25 C, 50	υ Α ι _{pk}	DIODE	1.20								

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$	1.0	
Typical turn-off time	t _q	I_{TM} = 300 A, T_J = T_J maximum, dI/dt = 20 A/μs, V_R = 50 V dV/dt = 20 V/μs, Gate 0 V 100 Ω , t_p = 500 μs	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 67 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{DRM} , I _{RRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	50	mA
RMS insulation voltage	V _{INS}	50 Hz, circuit to base, all terminal shorted, t = 1 s	3000	V



TRIGGERING						
PARAMETER	SYMBOL	VALUES	UNITS			
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms	10.0	W		
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$	2.0	VV		
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms	3.0	Α		
Maximum required DC gate voltage to trigger	V _{GT}		3	V		
Maximum required DC gate current to trigger	I _{GT}	T _J = 25 °C Anode supply: 12 V resistive load	200	mA		
Maximum holding current	I _H		600			
Maximum peak positive gate voltage	+V _{GM}	T - T maximum + < 5 mg	20	V		
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms	5.0] V		
DC gate voltage not to trigger	V_{GD}	$T_J = T_J \text{ maximum}$	0.30	V		
DC gate current not to trigger	I _{GD}	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	10	mA		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1 \mu s$ $T_J = T_J$ maximum, anode voltage $\le 80 \% V_{DRM}$	1000	A/μs		

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	YMBOL TEST CONDITIONS		UNITS		
Maximum junction operating temperature range		TJ	-40 to 140		°C		
Maximum storage tempera	ture range	T _{Stg}		-40 to 150			
Maximum thermal resistance, junction to case per junction		R _{thJC}	DC operation	0.19	K/W		
Maximum thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface smooth, flat and greased	0.035			
Mounting torque + 10 %	IAP to heatsink		A mounting compound is recommended and	4 to 6	Nies		
Mounting torque ± 10 %	busbar to IAP		A mounting compound is recommended and the torque should be rechecked after a	4 10 6	Nm		
Approximate weight			period of 3 hours to allow for the spread of the compound. Lubricated threads.	500	g		
Approximate weight			the compound. Eubhoated threads.	17.8	OZ.		
Case style				INT-A-F	PAK		

△R CONDUCTION PER JUNCTION											
DEVICES	SINUSOIDAL CONDUCTION AT T_J MAXIMUM				1	RECTANGULAR CONDUCTION AT TJ MAXIMUM				UNITS	
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
VSKL300	0.019	0.022	0.028	0.041	0.068	0.013	0.023	0.031	0.043	0.069	K/W

Note

• Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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Vishay Semiconductors

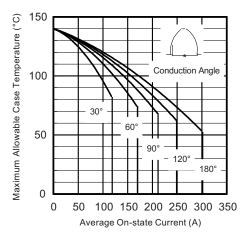


Fig. 1 - Current Ratings Characteristics

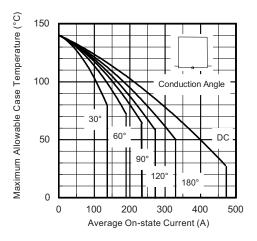


Fig. 2 - Current Ratings Characteristics

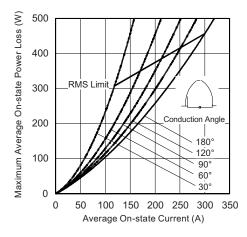


Fig. 3 - On-State Power Loss Characteristics

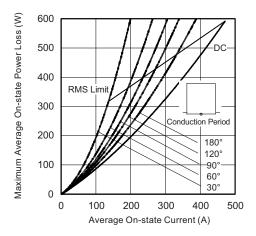


Fig. 4 - On-State Power Loss Characteristics

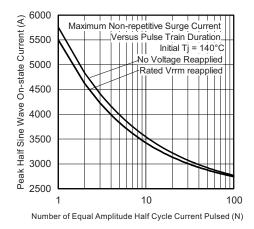


Fig. 5 - Maximum Non-Repetitive Surge Current

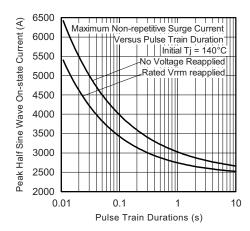
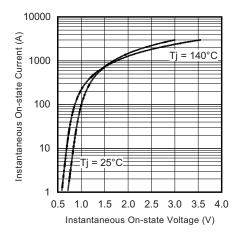


Fig. 6 - Maximum Non-Repetitive Surge Current





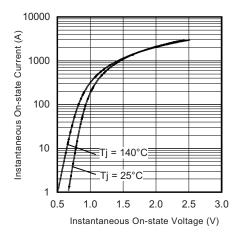


Fig. 8 - On-State Voltage Drop Characteristics (Diode)

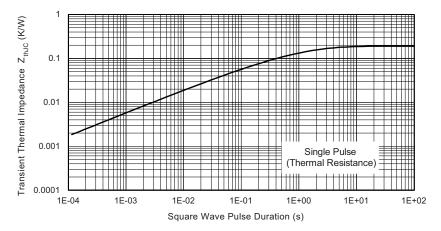
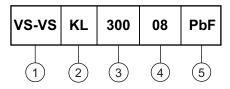


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Circuit configuration

- Current rating (300 = 300 A)

Voltage rating (08 = 800 V)

5 - PbF = Lead (Pb)-free



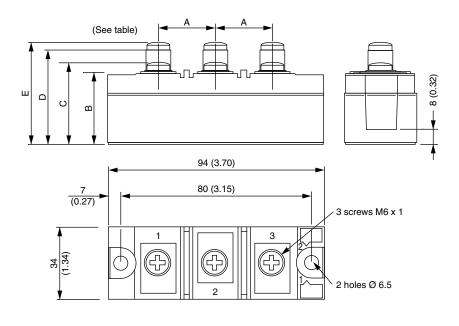
CIRCUIT CONFIGURATION					
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING			
SCR/diode doubler circuit, negative control	L	1 0 ~ 2 0 + 1 0 ~ 2 0 + 1 0 ~ 1 0 ~ 2 0 + 1 0 ~ 1			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95010			



INT-A-PAK Diode

DIMENSIONS in millimeters (inches)



Α	В	С	D	E
23 (0.91)	30 (1.18)	36 (1.42)	-	



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